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PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

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<b>Substitute for form 1449A/PTO</b> <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/726,529
				Filing Date	December 4, 2003
				First Named Inventor	Hongyong ZHANG
				Group Art Unit	2823
Examiner Name	K. Nguyen				
Sheet	1	of	4	Attorney Docket Number	740756-2675

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
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Examiner Signature: <u>Quoc Hoang</u>	Date Considered: <u>5/04</u>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.





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Form PTO-1449 (Rev. 8-83)	U.S. Department of Commerce Patent and Trademark Office	Attorney Docket: 740756-2675	Serial No. 10/726,529
<b>INFORMATION DISCLOSURE STATEMENT</b> (Use several sheets if necessary)		Applicant: Hongyong ZHANG	
		Filing Date: December 4, 2003	Group: 2823

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Examiner Signature: <i>Quir Hsuy</i>	Date Considered: <i>5/04</i>
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